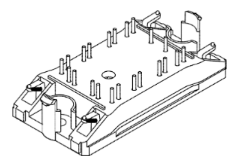
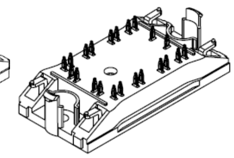
Dual Boost Power Module

NXH100B120H3Q0, NXH100B120H3Q0PG-R

The NXH100B120H3Q0 is a power module containing a dual boost stage. The integrated field stop trench IGBTs and SiC Diodes provide lower conduction losses and switching losses, enabling designers to achieve high efficiency and superior reliability.

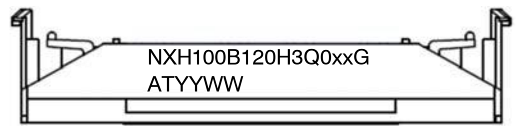


Q0BOOST
CASE 180AJ
SOLDER PINS



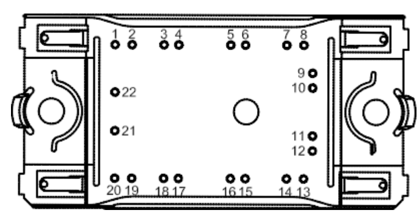
Q0BOOST
CASE 180BF
PRESS−FIT PINS

MARKING DIAGRAM



xx	= P, PT, S or ST
YYWW	= Year and Work Week Code
A	= Assembly Site Code
T	= Test Site Code
G	= Pb−Free Package

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

Features

- 1200 V Ultra Field Stop IGBTs
- Low Reverse Recovery and Fast Switching SiC Diodes
- 1600 V Bypass and Anti−parallel Diodes
- Low Inductive Layout
- Solderable Pins or Press−Fit Pins
- Thermistor
- Options with Pre−Applied Thermal Interface Material (TIM) and Without Pre−Applied TIM

Typical Applications

- Solar Inverter
- Uninterruptible Power Supplies
- Energy Storage Systems

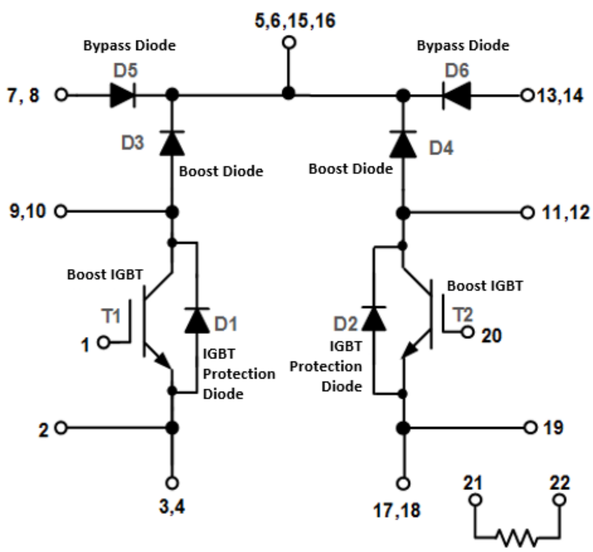


Figure 1. NXH100B120H3Q0xG/PG−R Schematic Diagram

January, 2022 − Rev. 7
Publication Order Number:
NXH100B120H3Q0/D

ABSOLUTE MAXIMUM RATINGS (Note 1) T_J = 25°C Unless Otherwise Noted

Rating	Symbol	Value	Unit
BOOST IGBT			
Collector−Emitter Voltage	V_{CES}	1200	V
Gate−Emitter Voltage	V_{GE}	±20	V
Continuous Collector Current @ T_C < 80°C (T_J = 175°C)	I_{C1}	61	A
Continuous Collector Current @ T_C < 102°C (T_J = 175°C)	I_{C2}	50	A
Pulsed Collector Current (T_J = 175°C)	I_{Cpulse}	150	A
Maximum Power Dissipation @ T_C = 80°C (T_J = 175°C)	P_{tot}	186	W
Minimum Operating Junction Temperature	T_{JMIN}	−40	°C
Maximum Operating Junction Temperature	T_{JMAX}	150	°C
BOOST DIODE			
Peak Repetitive Reverse Voltage	V_{RRM}	1200	V
Continuous Forward Current @ T_C < 80°C (T_J = 175°C)	I_{F1}	34	A
Continuous Forward Current @ T_C < 132°C (T_J = 175°C)	I_{F2}	20	A
Maximum Power Dissipation @ T_C = 80°C (T_J = 175°C)	P_{tot}	114	W
Surge Forward Current (60 Hz single half−sine wave)	I_{FSM}	185	A
I^2t − value (60 Hz single half−sine wave)	I^2t	142	A^2s
Minimum Operating Junction Temperature	T_{JMIN}	−40	°C
Maximum Operating Junction Temperature	T_{JMAX}	150	°C
BYPASS DIODE / IGBT PROTECTION DIODE			
Peak Repetitive Reverse Voltage	V_{RRM}	1600	V
Continuous Forward Current @ T_C < 80°C (T_J = 175°C)	I_{F1}	58	A
Continuous Forward Current @ T_C < 141°C (T_J = 175°C)	I_{F2}	25	A
Repetitive Peak Forward Current (T_J = 175°C, t_p limited by T_{Jmax})	I_{FRM}	75	A
Maximum Power Dissipation @ T_C = 80°C (T_J = 175°C)	P_{tot}	91	W
Minimum Operating Junction Temperature	T_{JMIN}	−40	°C
Maximum Operating Junction Temperature	T_{JMAX}	150	°C
THERMAL PROPERTIES			
Storage Temperature range	T_{stg}	−40 to 125	°C
INSULATION PROPERTIES			
Isolation test voltage, t = 1 sec, 60 Hz	V_{is}	3000	VRMS
Creepage distance		12.7	mm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

RECOMMENDED OPERATING RANGES

Rating	Symbol	Min	Max	Unit
Module Operating Junction Temperature	T_J	−40	150	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS T_J = 25°C Unless Otherwise Noted

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
BOOST IGBT CHARACTERISTICS						
Collector−Emitter Cutoff Current	V_{GE} = 0 V, V_{CE} = 1200 V	I_{CES}	–	–	200	μA
Collector−Emitter Saturation Voltage	V_{GE} = 15 V, I_C = 50 A, T_J = 25°C	$V_{CE(sat)}$	–	1.77	2.3	V
	V_{GE} = 15 V, I_C = 50 A, T_J = 150°C		–	1.93	–	
Gate−Emitter Threshold Voltage	V_{GE} = V_{CE}, I_C = 1 mA	$V_{GE(TH)}$	4.6	5.27	6.5	V
Gate Leakage Current	V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	–	–	800	nA
Turn−on Delay Time	T_J = 25°C V_{CE} = 700 V, I_C = 50 A V_{GE} = ±15 V, R_G = 4 Ω	$t_{d(on)}$	–	44	–	ns
Rise Time		t_r	–	16	–	
Turn−off Delay Time		$t_{d(off)}$	–	203	–	
Fall Time		t_f	–	23	–	
Turn−on Switching Loss per Pulse		E_{on}	–	700	–	
Turn−off Switching Loss per Pulse		E_{off}	–	1500	–	
Turn−on Delay Time	T_J = 125°C V_{CE} = 700 V, I_C = 50 A V_{GE} = ±15 V, R_G = 4 Ω	$t_{d(on)}$	–	43	–	ns
Rise Time		t_r	–	18	–	
Turn−off Delay Time		$t_{d(off)}$	–	233	–	
Fall Time		t_f	–	58	–	
Turn−on Switching Loss per Pulse		E_{on}	–	800	–	
Turn−off Switching Loss per Pulse		E_{off}	–	2600	–	
Input Capacitance	V_{CE} = 20 V, V_{GE} = 0 V, f = 10 kHz	C_{ies}	–	9075	–	pF
Output Capacitance		C_{oes}	–	173	–	
Reverse Transfer Capacitance		C_{res}	–	147	–	
Total Gate Charge	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V	Q_g	–	409	–	nC
Thermal Resistance − chip−to−case		R_{thJC}	–	0.51	–	°C/W
Thermal Resistance − chip−to−heatsink	Thermal grease, Thickness ≈ 100 μm, λ = 2.87 W/mK	R_{thJH}	–	0.82	–	°C/W
BOOST DIODE CHARACTERISTICS						
Diode Reverse Leakage Current	V_R = 1200 V	I_R	–	–	300	μA
Diode Forward Voltage	I_F = 20 A, T_J = 25°C	V_F	–	1.44	1.8	V
	I_F = 20 A, T_J = 150°C		–	1.93	–	
Reverse Recovery Time	T_J = 25°C V_{CE} = 700 V, I_C = 50 A V_{GE} = ±15 V, R_G = 4 Ω	t_{rr}	–	15	–	ns
Reverse Recovery Charge		Q_{rr}	–	108	–	nC
Peak Reverse Recovery Current		I_{RRM}	–	11	–	A
Peak Rate of Fall of Recovery Current		di/dt	–	1500	–	A/μs
Reverse Recovery Energy		E_{rr}	–	20	–	μJ
Reverse Recovery Time	T_J = 125°C V_{CE} = 700 V, I_C = 50 A V_{GE} = ±15 V, R_G = 4 Ω	t_{rr}	–	16	–	ns
Reverse Recovery Charge		Q_{rr}	–	115		nC
Peak Reverse Recovery Current		I_{RRM}	–	12		A
Peak Rate of Fall of Recovery Current		di/dt	–	1400		A/μs
Reverse Recovery Energy		E_{rr}	–	22		μJ
Thermal Resistance − chip−to−case		R_{thJC}	–	0.83		°C/W
Thermal Resistance − chip−to−heatsink	Thermal grease, Thickness ≈ 100 μm, λ = 2.87 W/mK	R_{thJH}	–	1.15	–	°C/W

ELECTRICAL CHARACTERISTICS T_J = 25°C Unless Otherwise Noted

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
BYPASS DIODE/IGBT PROTECTION DIODE CHARACTERISTICS						
Diode Reverse Leakage Current	V_R = 1600 V, T_J = 25°C	I_R	–	–	100	μA
Diode Forward Voltage	I_F = 25 A, T_J = 25°C	V_F	–	1.0	1.4	V
	I_F = 25 A, T_J = 150°C		–	0.90	–	
Thermal Resistance − chip−to−case		R_{thJC}	–	1.04	–	°C/W
Thermal Resistance − chip−to−heatsink	Thermal grease, Thickness ≈ 100 μm, λ = 2.87 W/mK	R_{thJH}	–	1.41	–	°C/W
THERMISTOR CHARACTERISTICS						
Nominal resistance		R_{25}	–	22	–	kΩ
Nominal resistance	T = 100°C	R_{100}	–	1486	–	Ω
Deviation of R25		ΔR/R	−5	–	5	%
Power dissipation		P_D	–	200	–	mW
Power dissipation constant			–	2	–	mW/K
B−value	B(25/50), tolerance ±3%		–	3950	–	K
B−value	B(25/100), tolerance ±3%		–	3998	–	K

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Orderable Part Number	Marking	Package	Shipping
NXH100B120H3Q0PG, NXH100B120H3Q0PG−R	NXH100B120H3Q0PG, NXH100B120H3Q0PG−R	Q0BOOST − Case 180BF (Pb−Free and Halide−Free) Press−Fit Pins	24 Units / Blister Tray
NXH100B120H3Q0SG	NXH100B120H3Q0SG	Q0BOOST − Case 180AJ (Pb−Free and Halide−Free) Solder Pins	24 Units / Blister Tray
NXH100B120H3Q0PTG	NXH100B120H3Q0PTG	Q0BOOST − Case 180BF (Pb−Free and Halide−Free) Press−Fit Pins, Thermal Interface Material (TIM)	24 Units / Blister Tray
NXH100B120H3Q0STG	NXH100B120H3Q0STG	Q0BOOST − Case 180AJ (Pb−Free and Halide−Free) Solder Pins, Thermal Interface Material (TIM)	24 Units / Blister Tray

TYPICAL CHARACTERISTICS
Boost IGBT & IGBT Protection Diode / Bypass Diode

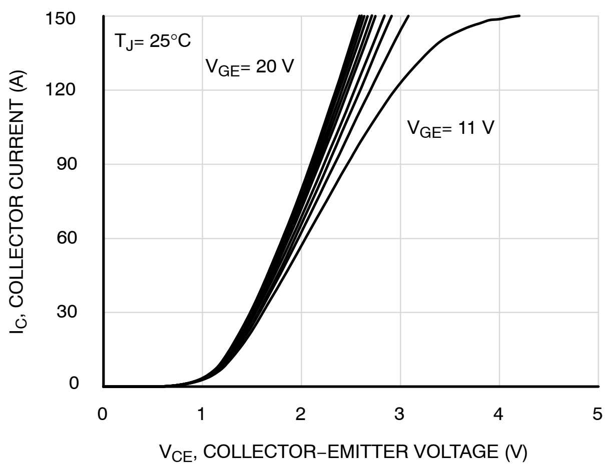


Figure 2. IGBT Typical Output Characteristics

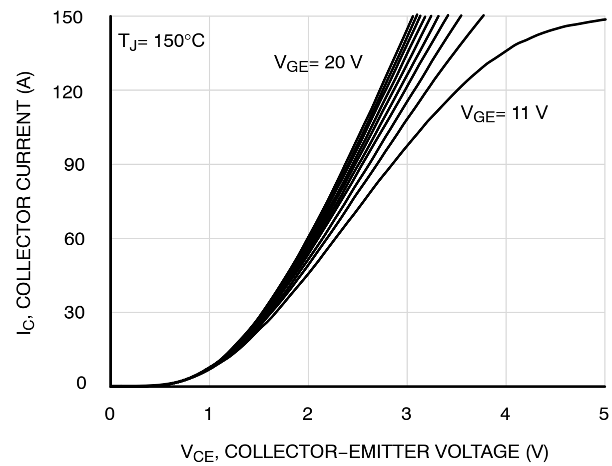


Figure 3. IGBT Typical Output Characteristics

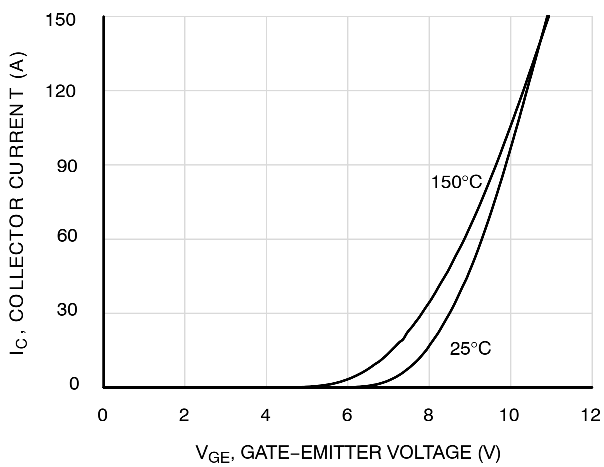


Figure 4. IGBT Typical Transfer Characteristics

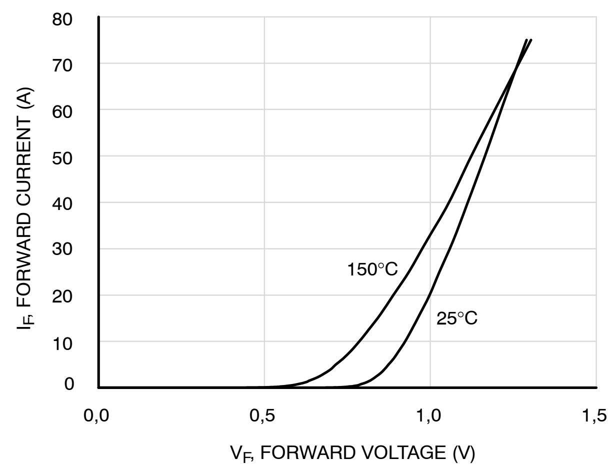


Figure 5. Diode Forward Characteristics

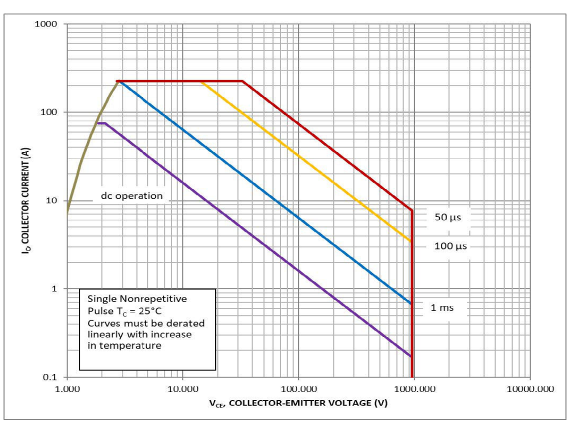


Figure 6. FBSOA

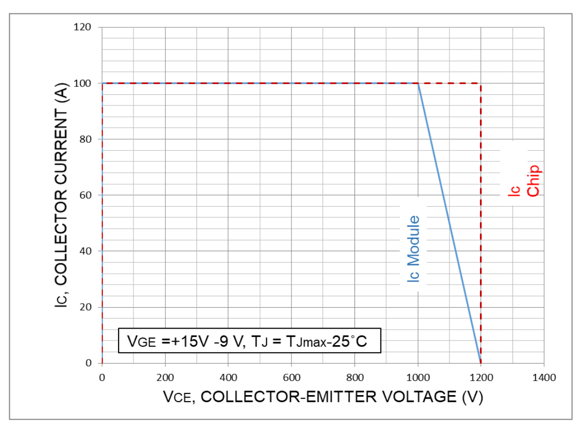


Figure 7. RBSOA

TYPICAL CHARACTERISTICS
Boost IGBT & IGBT Protection Diode / Bypass Diode

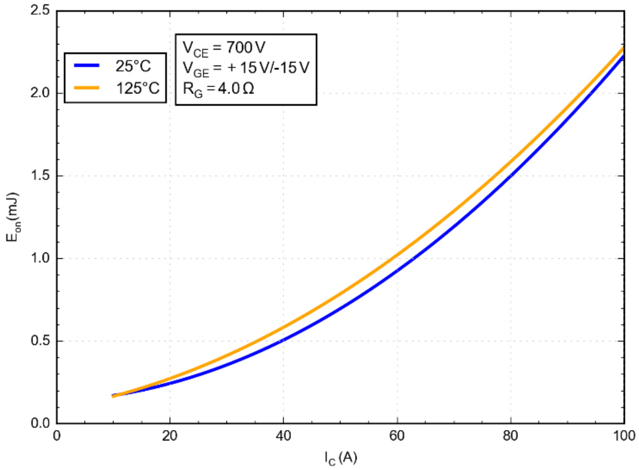


Figure 8. Typical Switching Loss Eon vs. IC

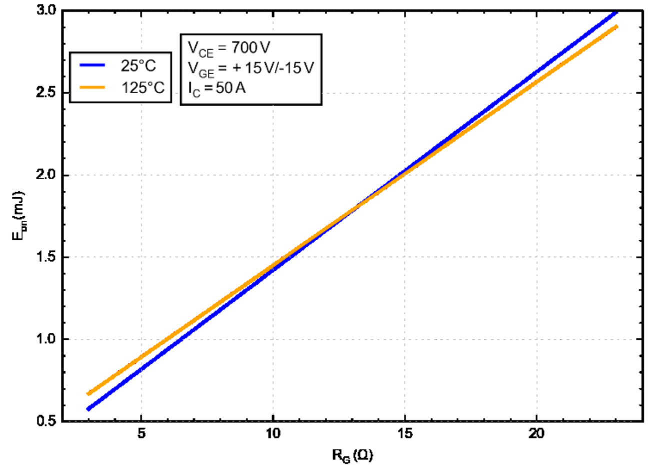


Figure 9. Typical Switching Loss Eon vs. R_G

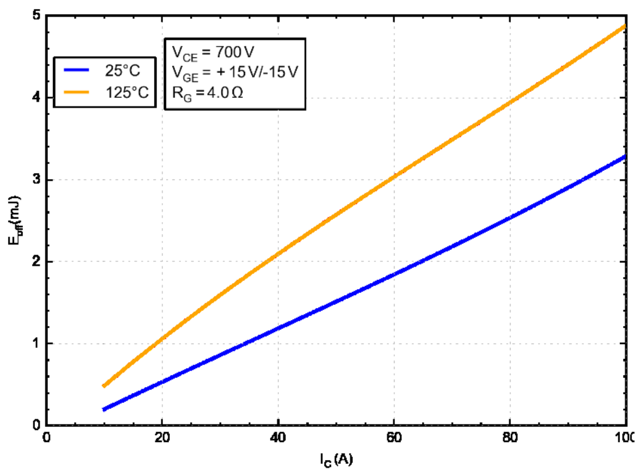


Figure 10. Typical Switching Loss Eoff vs. IC

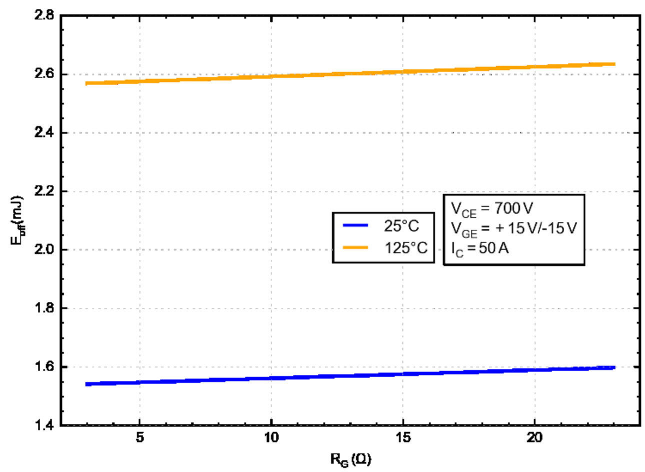


Figure 11. Typical Switching Loss Eoff vs. R_G

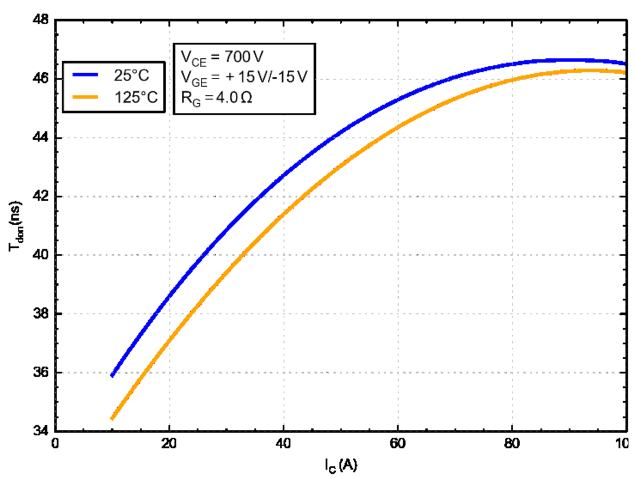


Figure 12. Typical Switching Time Tdon vs. IC

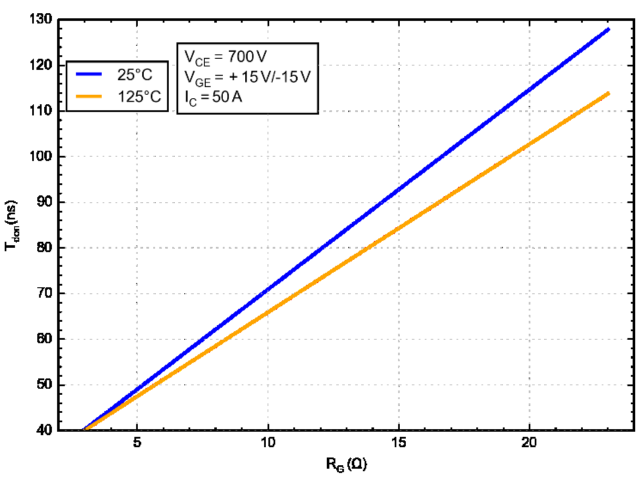


Figure 13. Typical Switching Time Tdon vs. R_G

TYPICAL PERFORMANCE CHARACTERISTICS

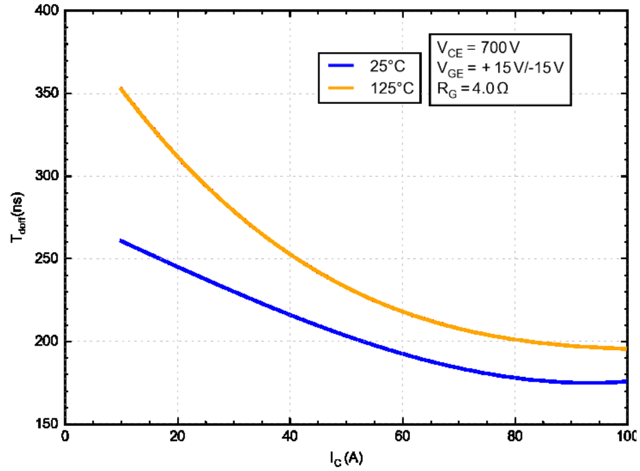


Figure 14. Typical Switching Time Tdoff vs. IC

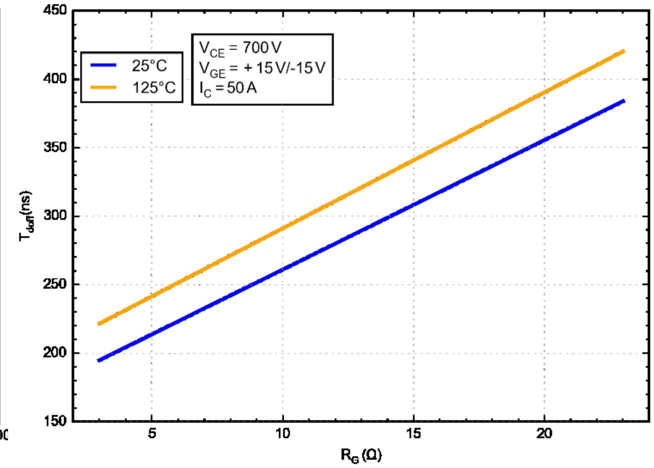


Figure 15. Typical Switching Time Tdoff vs. R_G

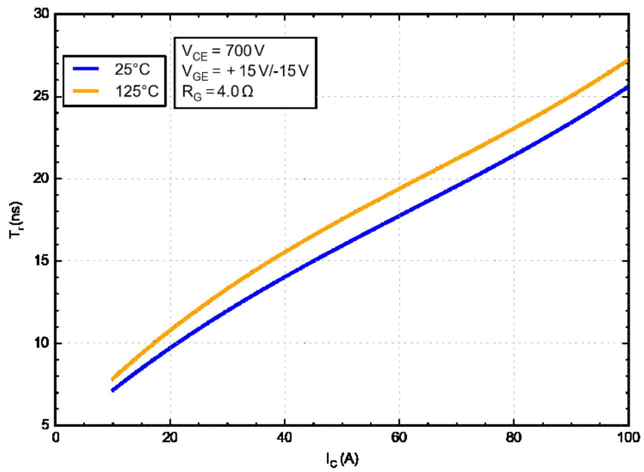


Figure 16. Typical Switching Time Tron vs. IC

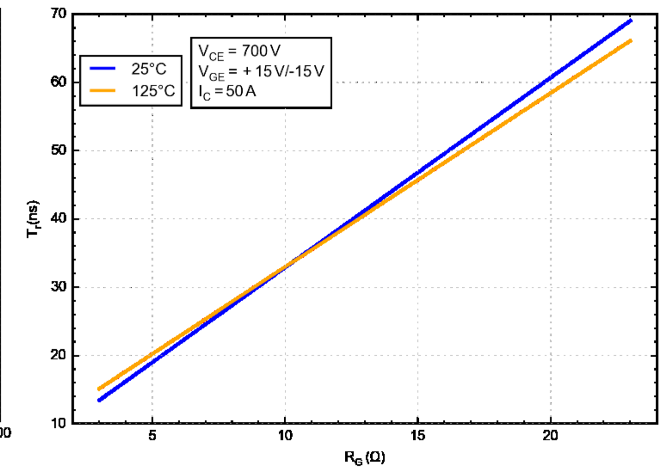


Figure 17. Typical Switching Time Tron vs. R_G

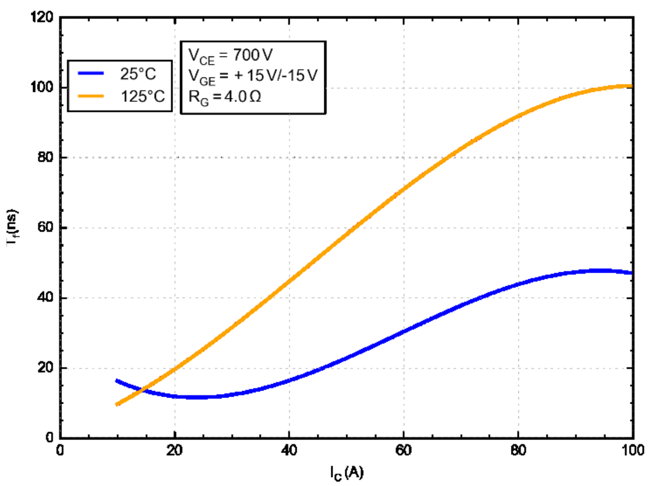


Figure 18. Typical Switching Time Tf vs. IC

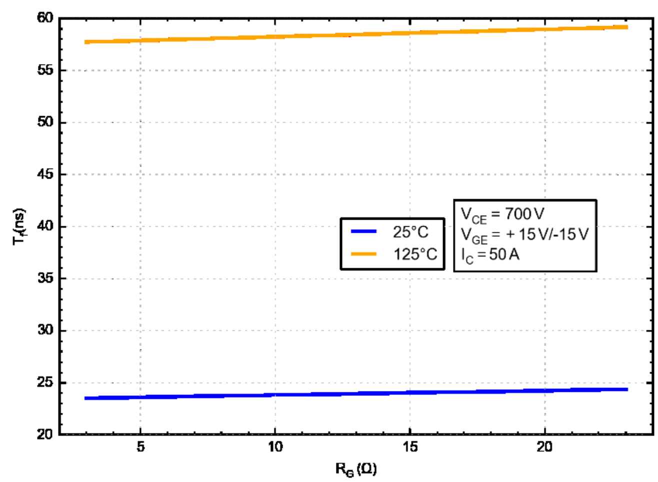


Figure 19. Typical Switching Time Tf vs R_G

TYPICAL PERFORMANCE CHARACTERISTICS

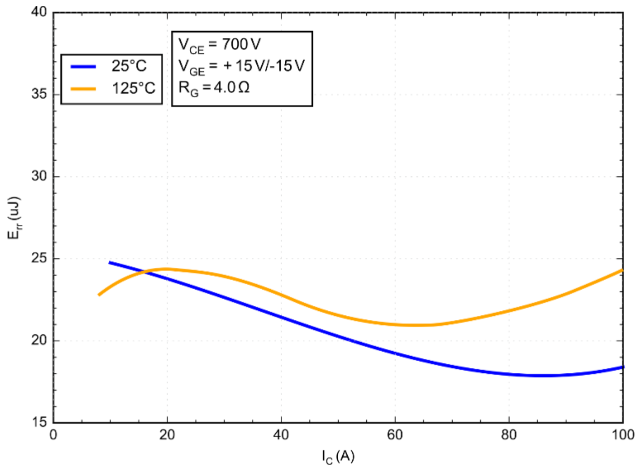


Figure 20. Typical Reverse Recovery Energy vs. IC

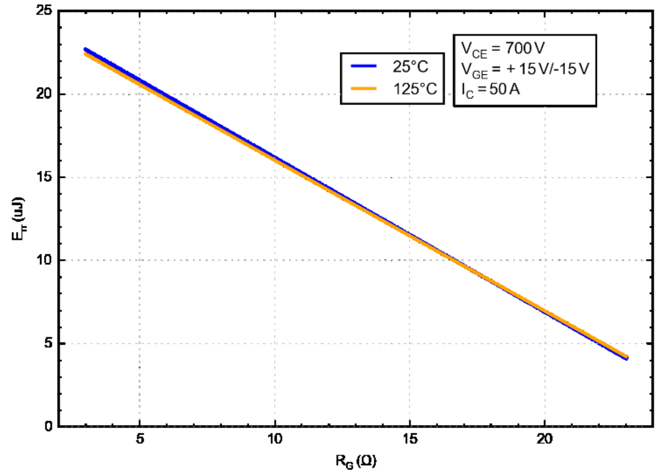


Figure 21. Typical Reverse Recovery Energy vs. RG

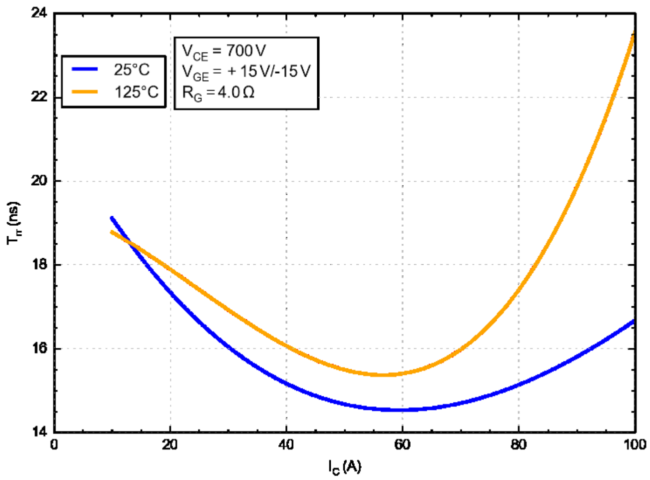


Figure 22. Typical Reverse Recovery Time vs. IC

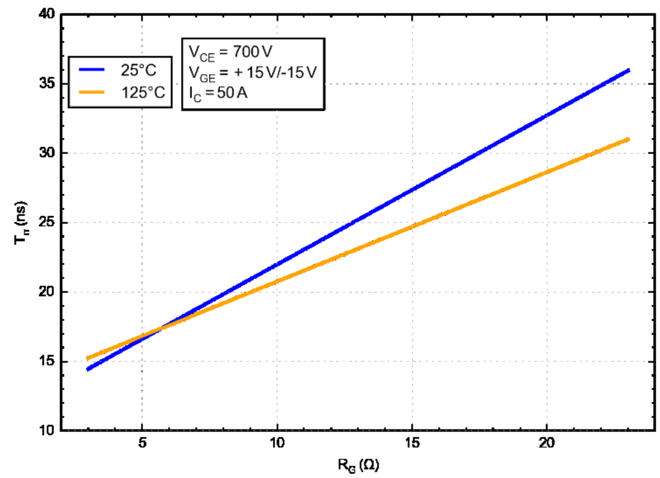


Figure 23. Typical Reverse Recovery Time vs. RG

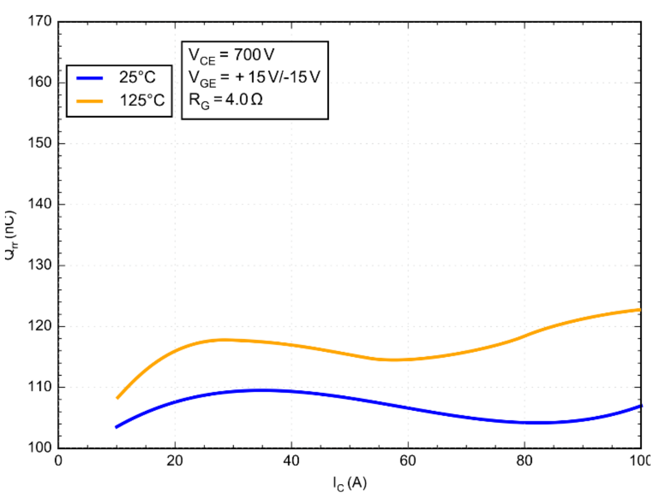


Figure 24. Typical Reverse Recovery Charge vs. IC

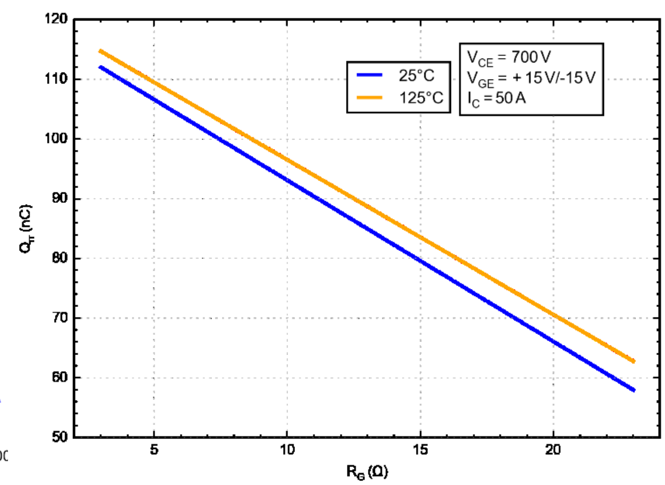


Figure 25. Typical Reverse Recovery Charge vs. RG

TYPICAL PERFORMANCE CHARACTERISTICS

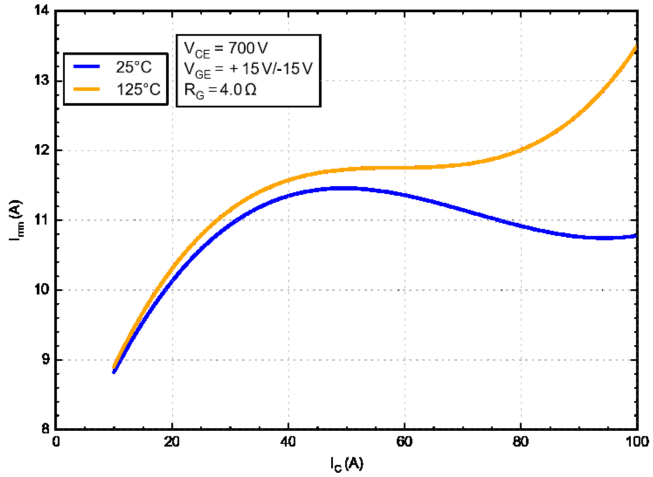


Figure 26. Typical Reverse Recovery Current vs. IC

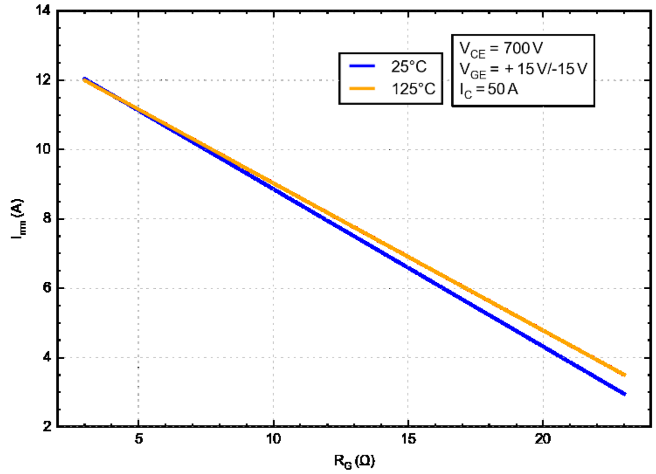


Figure 27. Typical Reverse Recovery Current vs. RG

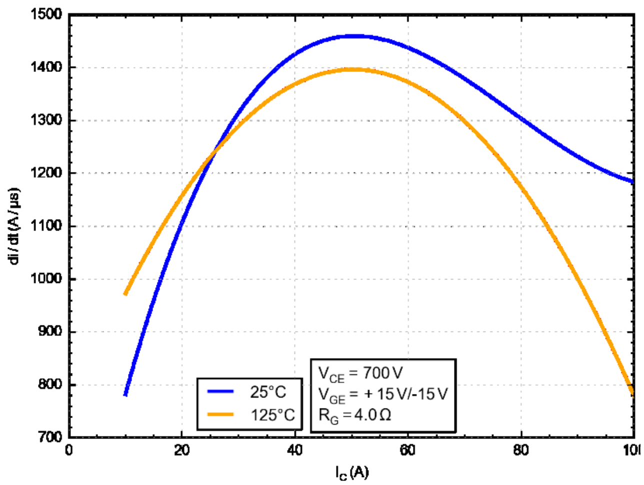


Figure 28. Typical di/dt vs. IC

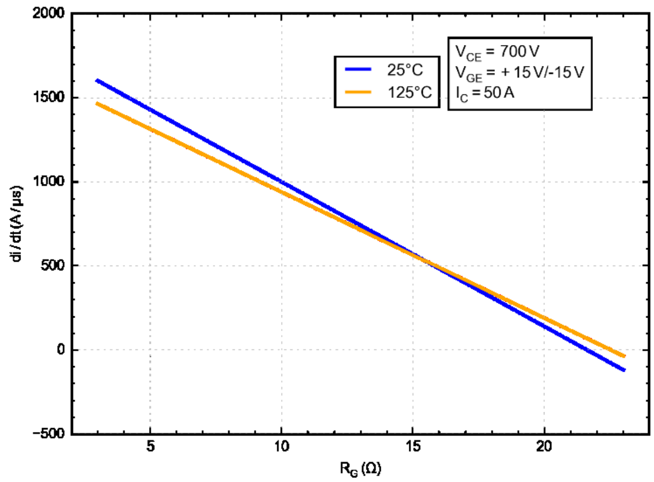


Figure 29. Typical di/dt vs.R_G

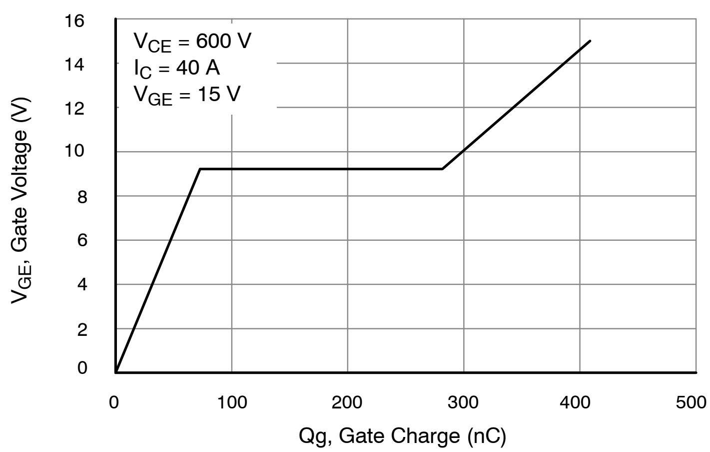


Figure 30. Gate Voltage vs. Gate Charge

TYPICAL PERFORMANCE CHARACTERISTICS

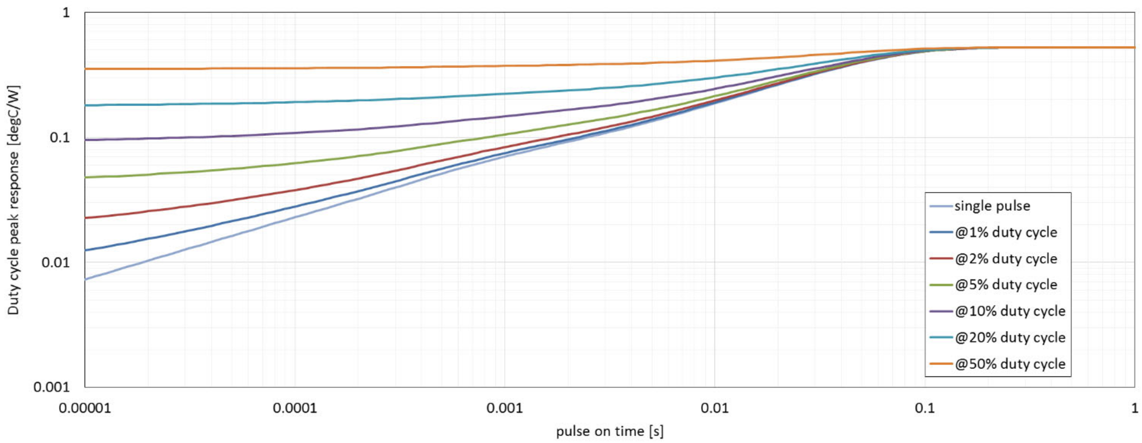


Figure 31. IGBT Junction−to−Case Transient Thermal Impedance

TYPICAL PERFORMANCE CHARACTERISTICS − Boost Diode

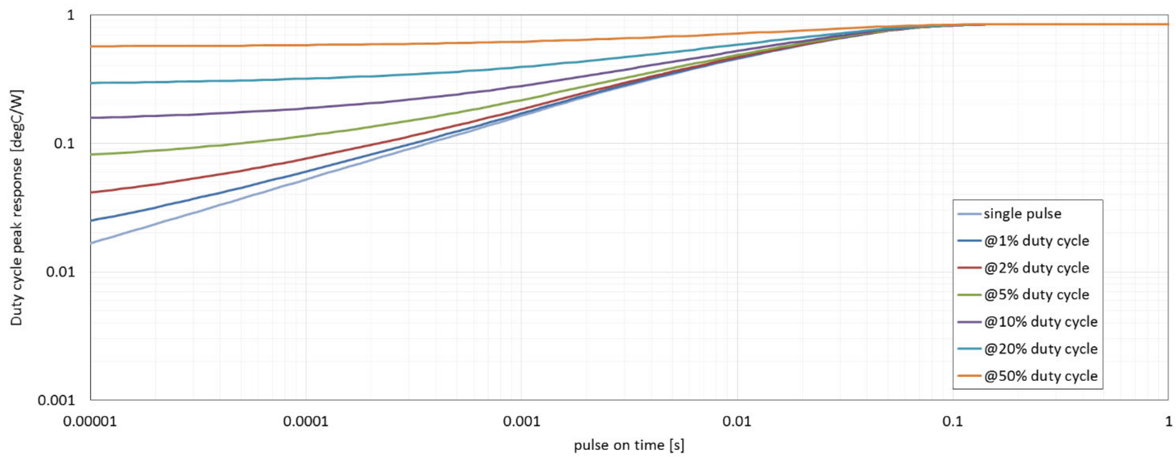


Figure 32. Diode Junction−to−Case Transient Thermal Impedance

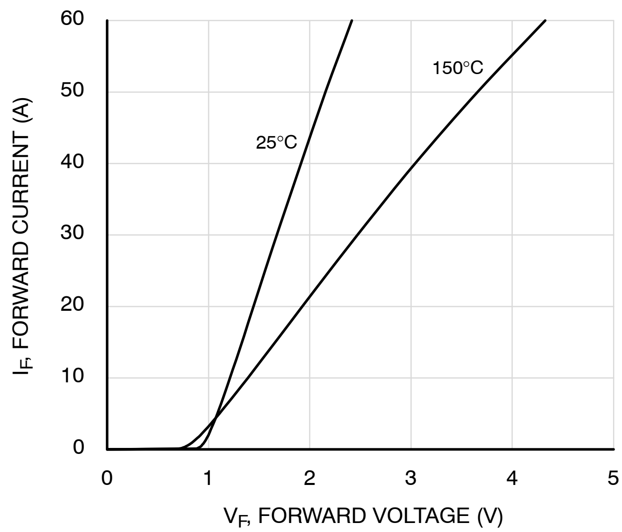


Figure 33. Diode Forward Characteristic

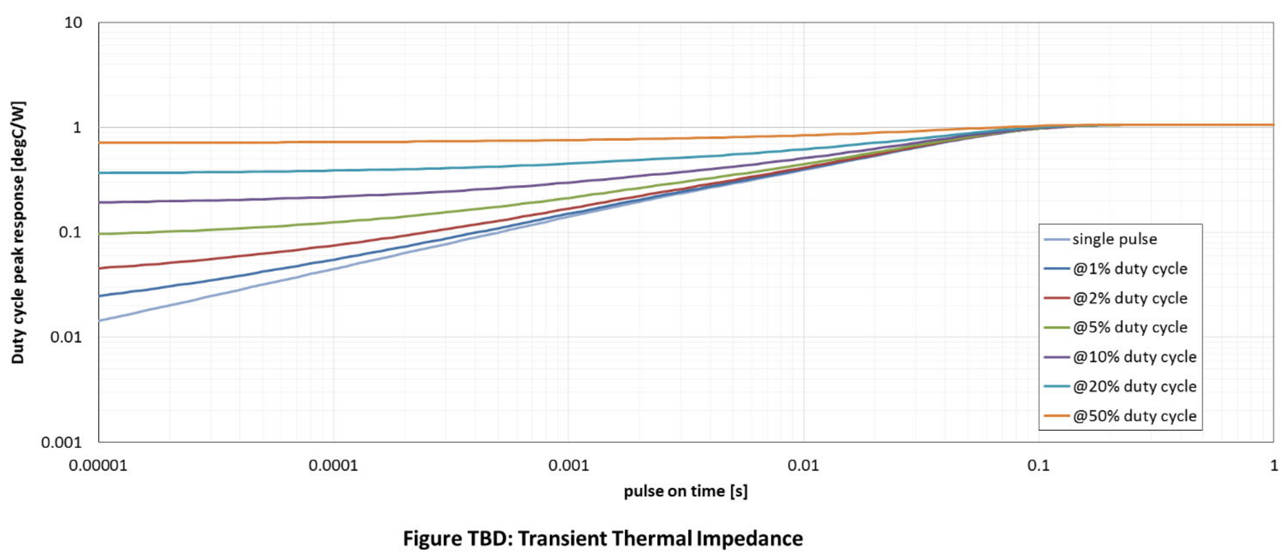
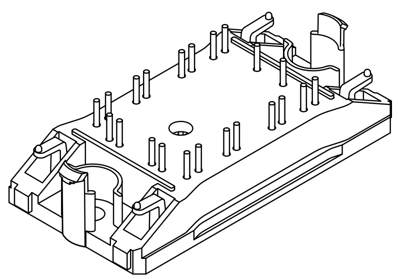
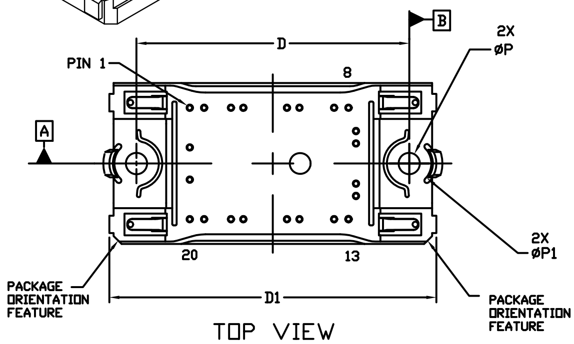


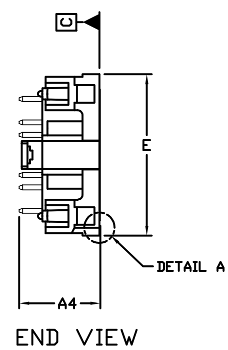
Figure 34. Diode Junction−to−Case Transient Thermal Impedance

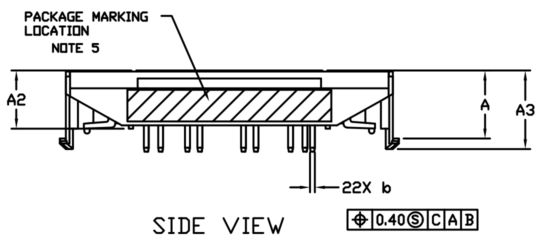


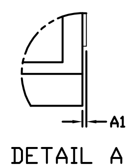
PIM22, 55x32.5 / Q0BOOST
CASE 180AJ
ISSUE B

DATE 08 NOV 2017









NOTES:

1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 1.00 AND 3.00 FROM THE TERMINAL TIP.
4. POSITION OF THE CENTER OF THE TERMINALS IS DETERMINED FROM DATUM B THE CENTER OF DIMENSION D, X DIRECTION, AND FROM DATUM A, Y DIRECTION. POSITIONAL TOLERANCE, AS NOTED IN DRAWING, APPLIES TO EACH TERMINAL IN BOTH DIRECTIONS.
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.

DIM	MILLIMETERS MIN.	NOM.
A	13.50	13.90
A1	0.10	0.30
A2	11.50	11.90
A3	15.65	16.05
A4	16.35 REF	
b	0.95	1.05
D	54.80	55.20
D1	65.60	66.20
E	32.20	32.80
P	4.20	4.40
P1	8.90	9.10

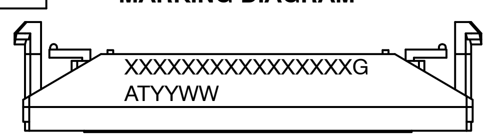
MOUNTING HOLE POSITION

PIN	HOLE POSITION X	Y	PIN	PIN POSITION X	Y
1	−16.75	−11.25	12	16.75	6.55
2	−13.85	−11.25	13	15.25	11.25
3	−8.45	−11.25	14	12.35	11.25
4	−5.95	−11.25	15	5.35	11.25
5	2.85	−11.25	16	2.85	11.25
6	5.35	−11.25	17	−5.95	11.25
7	12.35	−11.25	18	−8.45	11.25
8	15.25	−11.25	19	−13.85	11.25
9	16.75	−6.55	20	−16.75	11.25
10	16.75	−4.05	21	−16.75	3.25
11	16.75	4.05	22	−16.75	−3.25

NOTE 4

PIN	PIN POSITION X	Y	PIN	PIN POSITION X	Y
1	−16.75	11.25	12	16.75	−6.55
2	−13.85	11.25	13	15.25	−11.25
3	−8.45	11.25	14	12.35	−11.25
4	−5.95	11.25	15	5.35	−11.25
5	2.85	11.25	16	2.85	−11.25
6	5.35	11.25	17	−5.95	−11.25
7	12.35	11.25	18	−8.45	−11.25
8	15.25	11.25	19	−13.85	−11.25
9	16.75	6.55	20	−16.75	−11.25
10	16.75	4.05	21	−16.75	−3.25
11	16.75	−4.05	22	−16.75	3.25

GENERIC MARKING DIAGRAM*



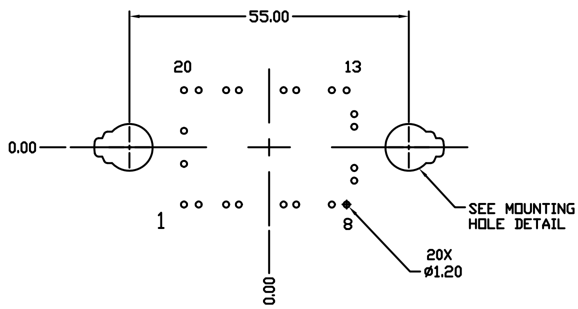
XXXXX = Specific Device Code
G = Pb−Free Package
AT = Assembly & Test Site Code
YYWW = Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

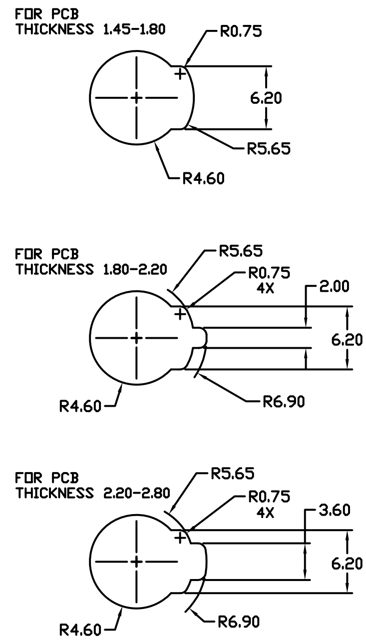
DOCUMENT NUMBER:	98AON63481G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	PIM22 55X32.5 / Q0BOOST (SOLDER PIN)	PAGE 1 OF 2

PIM22, 55x32.5 / Q0BOOST
CASE 180AJ
ISSUE B

DATE 08 NOV 2017

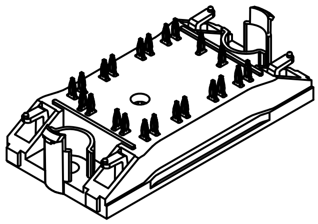


RECOMMENDED
MOUNTING PATTERN



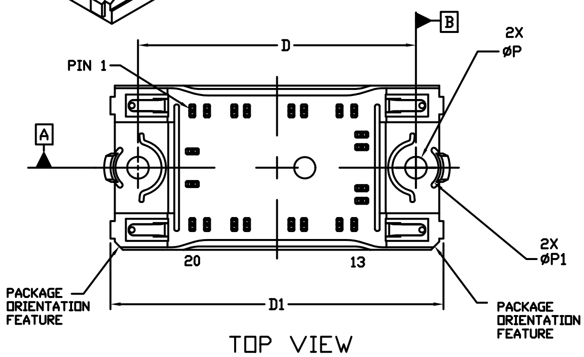
MOUNTING HOLE DETAIL

DOCUMENT NUMBER:	98AON63481G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	PIM22 55X32.5 / Q0BOOST (SOLDER PIN)	PAGE 2 OF 2

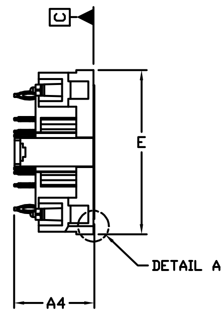


PIM22 55x32.5 (PRESSFIT PIN)
CASE 180BF
ISSUE O

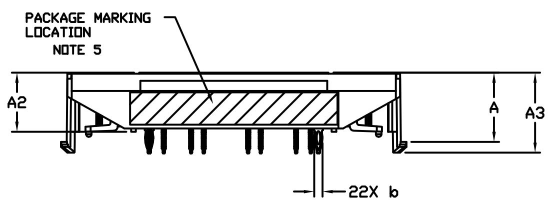
DATE 21 MAY 2019



TOP VIEW



END VIEW



SIDE VIEW

⌖ 0.40Ⓢ C A B

NOTES:

1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 1.00 AND 3.00 FROM THE TERMINAL TIP.
4. POSITION OF THE CENTER OF THE TERMINALS IS DETERMINED FROM DATUM B THE CENTER OF DIMENSION D, X DIRECTION, AND FROM DATUM A, Y DIRECTION. POSITIONAL TOLERANCE, AS NOTED IN DRAWING, APPLIES TO EACH TERMINAL IN BOTH DIRECTIONS.
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	13.50	13.70	13.90
A1	0.10	0.20	0.30
A2	11.50	11.70	11.90
A3	15.65	15.85	16.05
A4	15.95 REF		
b	1.61	1.66	1.71
D	54.80	55.00	55.20
D1	65.60	65.90	66.20
E	32.20	32.50	32.80
P	4.20	4.30	4.40
P1	8.90	9.00	9.10

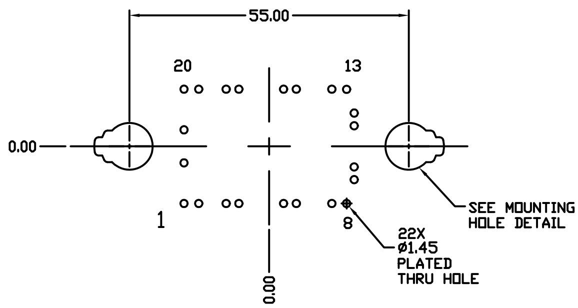
NOTE 4

	PIN POSITION			PIN POSITION	
PIN	X	Y	PIN	X	Y
1	−16.75	11.25	12	16.75	−6.55
2	−13.85	11.25	13	15.25	−11.25
3	−8.45	11.25	14	12.35	−11.25
4	−5.95	11.25	15	5.35	−11.25
5	2.85	11.25	16	2.85	−11.25
6	5.35	11.25	17	−5.95	−11.25
7	12.35	11.25	18	−8.45	−11.25
8	15.25	11.25	19	−13.85	−11.25
9	16.75	6.55	20	−16.75	−11.25
10	16.75	4.05	21	−16.75	−3.25
11	16.75	−4.05	22	−16.75	3.25

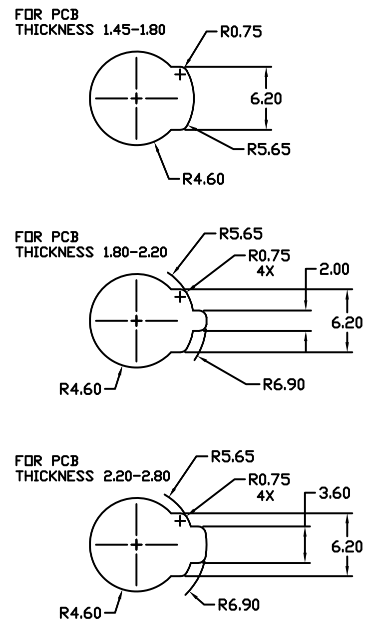
DOCUMENT NUMBER:	98AON07824H	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	PIM22 55x32.5 (PRESSFIT PIN)		PAGE 1 OF 2

MOUNTING HOLE POSITION

	HOLE POSITION			PIN POSITION	
PIN	X	Y	PIN	X	Y
1	−16.75	−11.25	12	16.75	6.55
2	−13.85	−11.25	13	15.25	11.25
3	−8.45	−11.25	14	12.35	11.25
4	−5.95	−11.25	15	5.35	11.25
5	2.85	−11.25	16	2.85	11.25
6	5.35	−11.25	17	−5.95	11.25
7	12.35	−11.25	18	−8.45	11.25
8	15.25	−11.25	19	−13.85	11.25
9	16.75	−6.55	20	−16.75	11.25
10	16.75	−4.05	21	−16.75	3.25
11	16.75	4.05	22	−16.75	−3.25

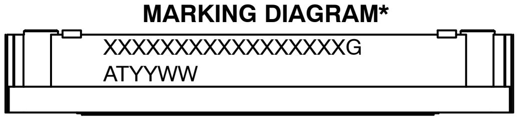


RECOMMENDED MOUNTING PATTERN



MOUNTING HOLE DETAIL

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
G = Pb−Free Package
AT = Assembly & Test Site Code
YYWW = Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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